FAIRCHILD SEMICONDUCTOR®

October 2006

UniFET™

FDA75N28

280V N-Channel MOSFET

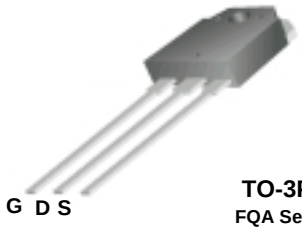
Features

- 75A, 280V, $R_{DS(on)}$ = 0.041Ω @V_{GS} = 10 V
- Low gate charge (typical 111 nC)
- Low C_{rss} (typical 90 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

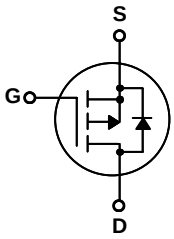
Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficient switched mode power supplies and active power factor correction.



TO-3PN
FQA Series



Absolute Maximum Ratings

Symbol	Parameter		FDA75N28	Unit
V_{DSS}	Drain-Source Voltage		280	V
I_D	Drain Current	- Continuous (T_C = 25°C) - Continuous (T_C = 100°C)	75 45	A A
I_{DM}	Drain Current	- Pulsed (Note 1)	300	A
V_{GSS}	Gate-Source voltage		± 30	V
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	3080	mJ
I_{AR}	Avalanche Current	(Note 1)	75	A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	52	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5	V/ns
P_D	Power Dissipation	(T_C = 25°C) - Derate above 25°C	520 4.2	W W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		300	°C

* Drain current limited by maximum junction termperature.

Thermal Characteristics

Symbol	Parameter	Min.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	0.24	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink	0.24	--	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	40	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDA75N28	FDA75N28	TO-3PN	--	--	30

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250μA	280	--	--	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250μA, Referenced to 25°C	--	0.28	--	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 280V, V_{GS} = 0V V_{DS} = 224V, T_C = 125°C	-- --	-- --	1 10	μA μA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 30V, V_{DS} = 0V	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -30V, V_{DS} = 0V	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 10V, I_D = 37.5A	--	0.035	0.041	Ω
g_{FS}	Forward Transconductance	V_{DS} = 40V, I_D = 37.5A (Note 4)	--	75	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz	--	5040	6700	pF
C_{oss}	Output Capacitance		--	915	1215	pF
C_{rss}	Reverse Transfer Capacitance		--	90	135	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 140V, I_D = 75A R_G =25Ω (Note 4, 5)	--	105	146	ns
t_r	Turn-On Rise Time		--	580	538	ns
$t_{d(off)}$	Turn-Off Delay Time		--	190	418	ns
t_f	Turn-Off Fall Time		--	310	262	ns
Q_g	Total Gate Charge	V_{DS} = 224V, I_D = 75A V_{GS} = 10V (Note 4, 5)	--	111	144	nC
Q_{gs}	Gate-Source Charge		--	31	--	nC
Q_{gd}	Gate-Drain Charge		--	49	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	75	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	300	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0V, I_S = 75A	--	--	1.4	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0V, I_S = 75A dI_F/dt =100A/μs (Note 4)	--	320	--	ns
Q_{rr}	Reverse Recovery Charge		--	3.5	--	μC

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L = 0.9mH, I_{AS} = 75A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
3. I_{SD} ≤ 75A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%
5. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

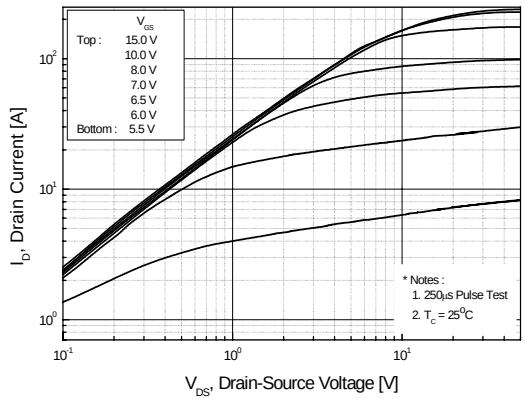


Figure 2. Transfer Characteristics

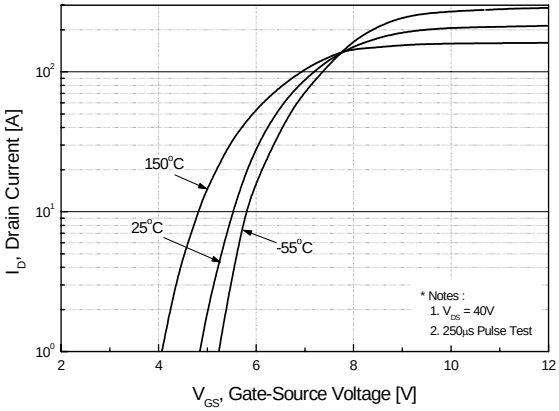


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

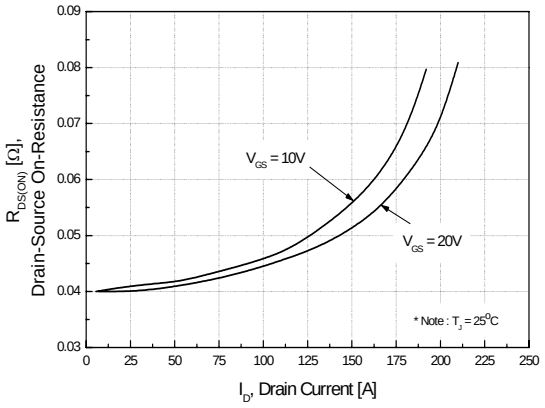


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

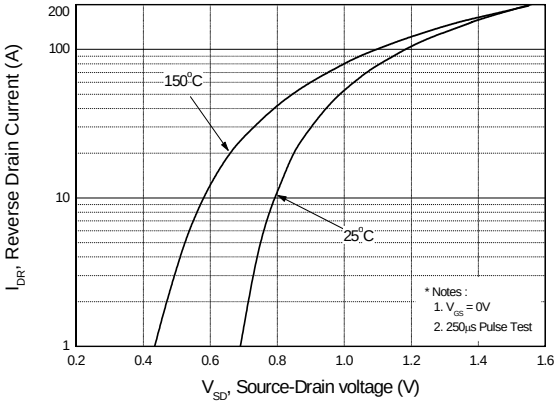


Figure 5. Capacitance Characteristics

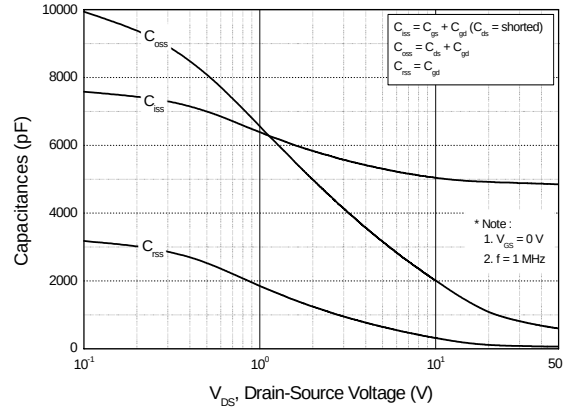
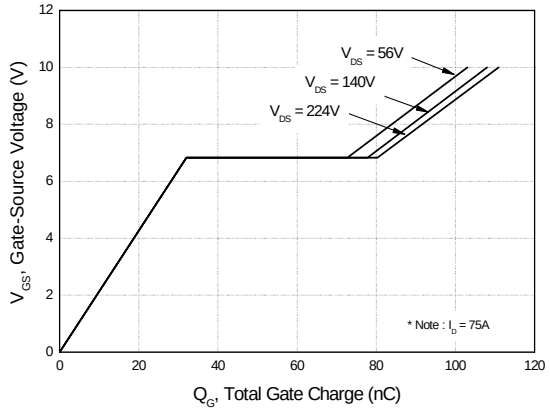


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

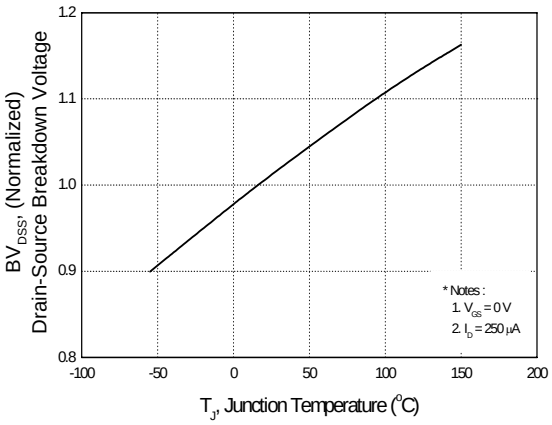


Figure 8. On-Resistance Variation vs. Temperature

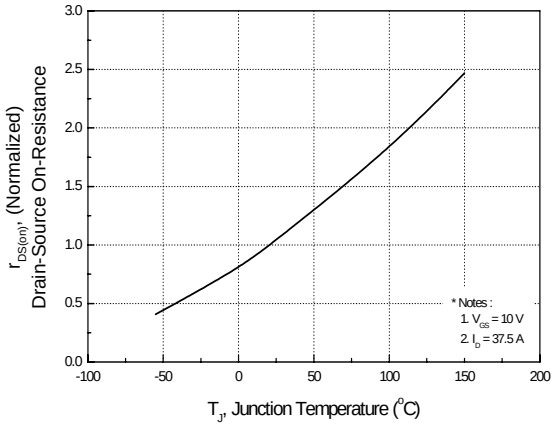


Figure 9. Safe Operating Area

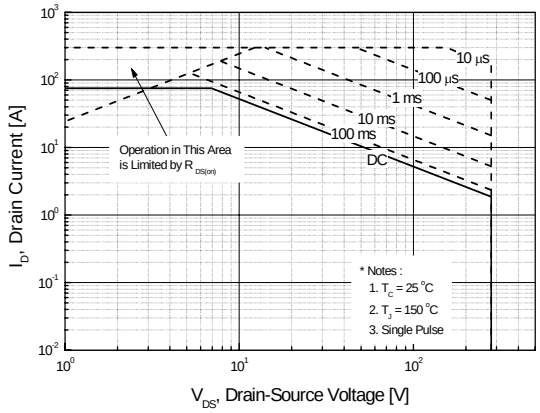


Figure 10. Maximum Drain Current vs. Case Temperature

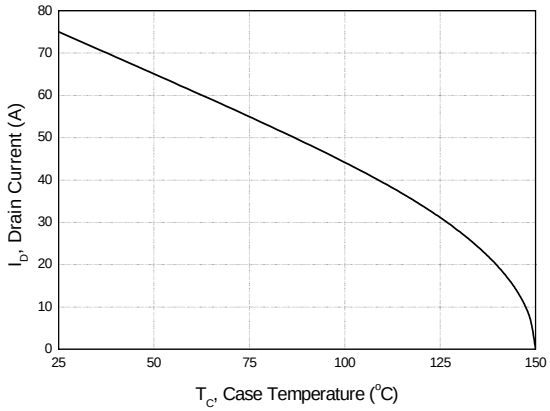
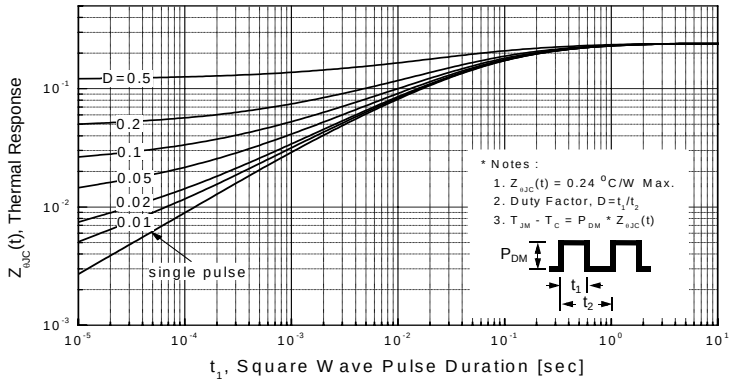
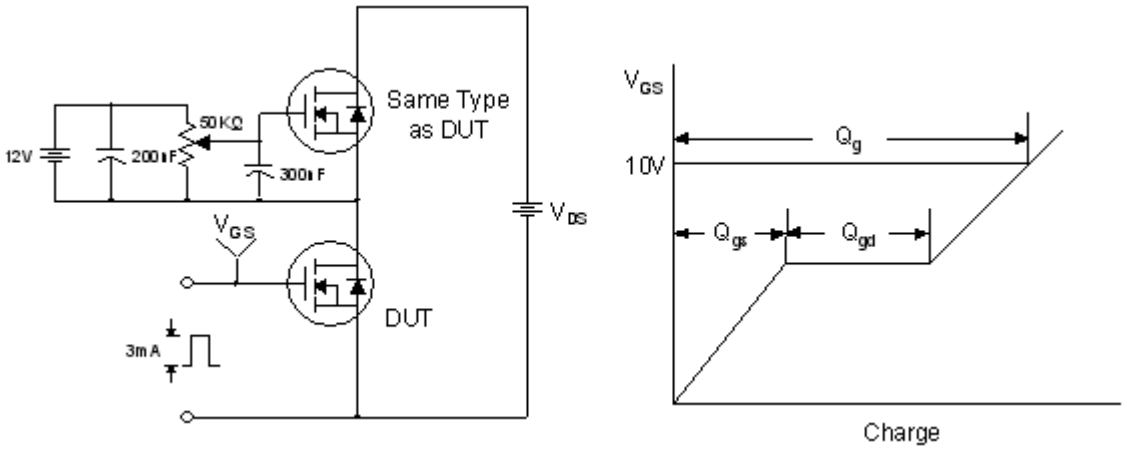


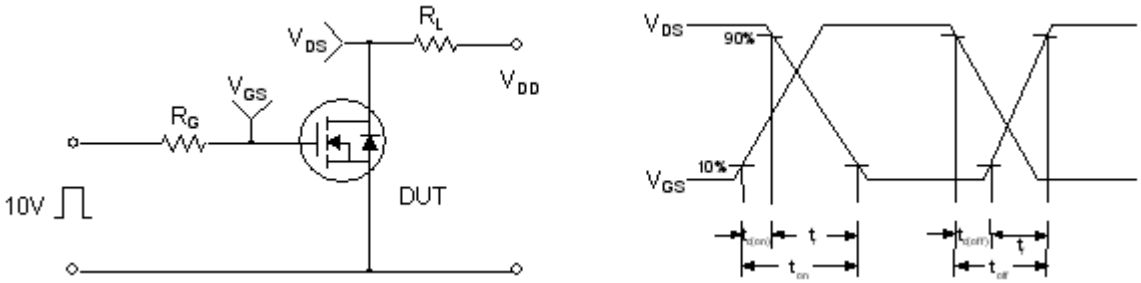
Figure 11. Transient Thermal Response Curve



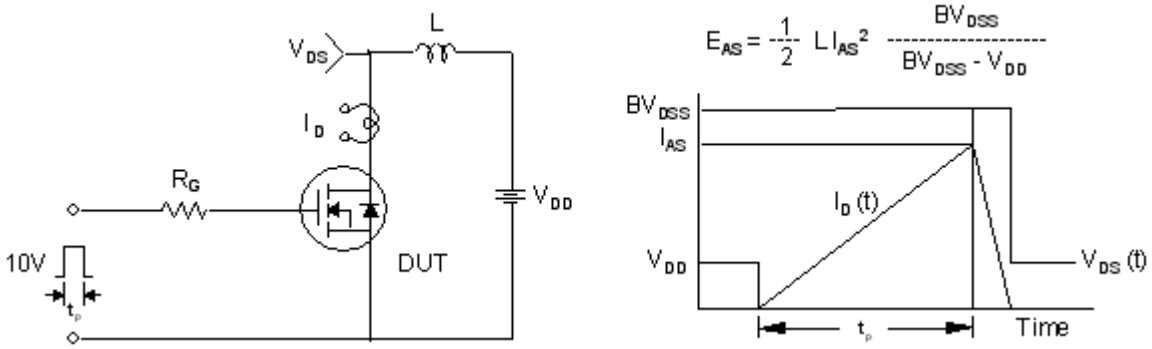
Gate Charge Test Circuit & Waveform



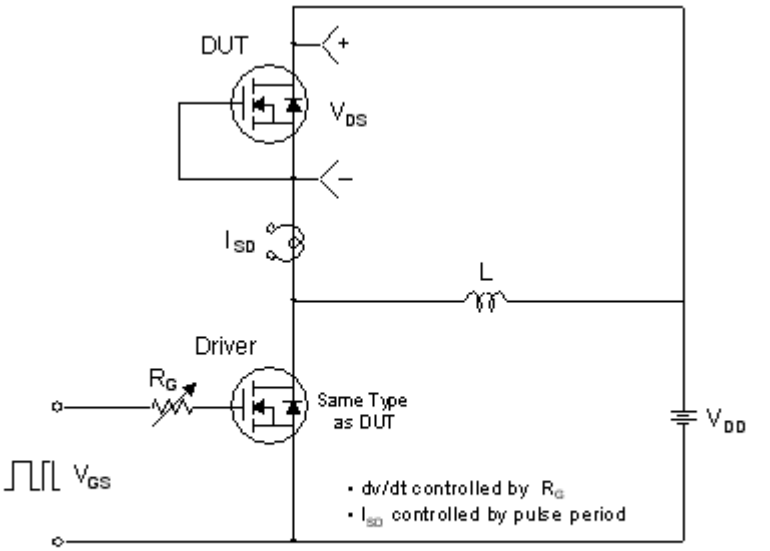
Resistive Switching Test Circuit & Waveforms

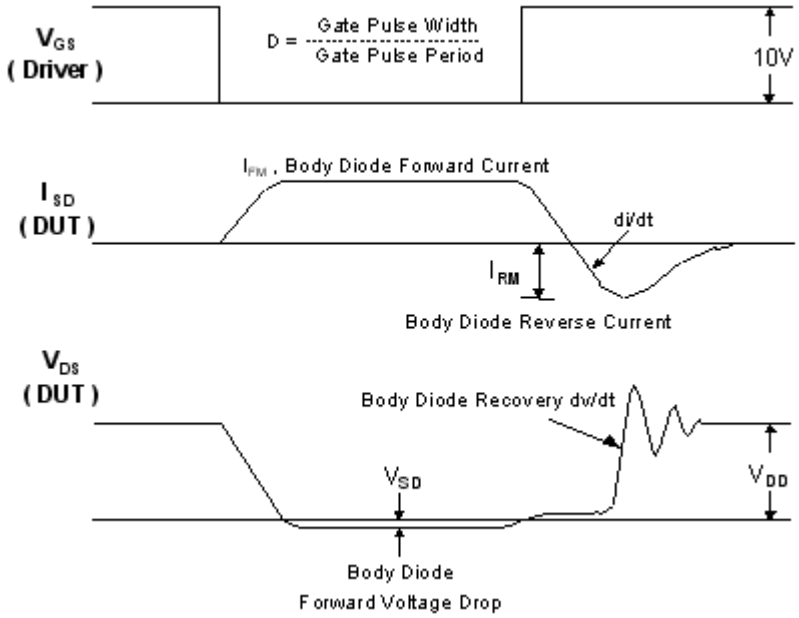


Unclamped Inductive Switching Test Circuit & Waveforms



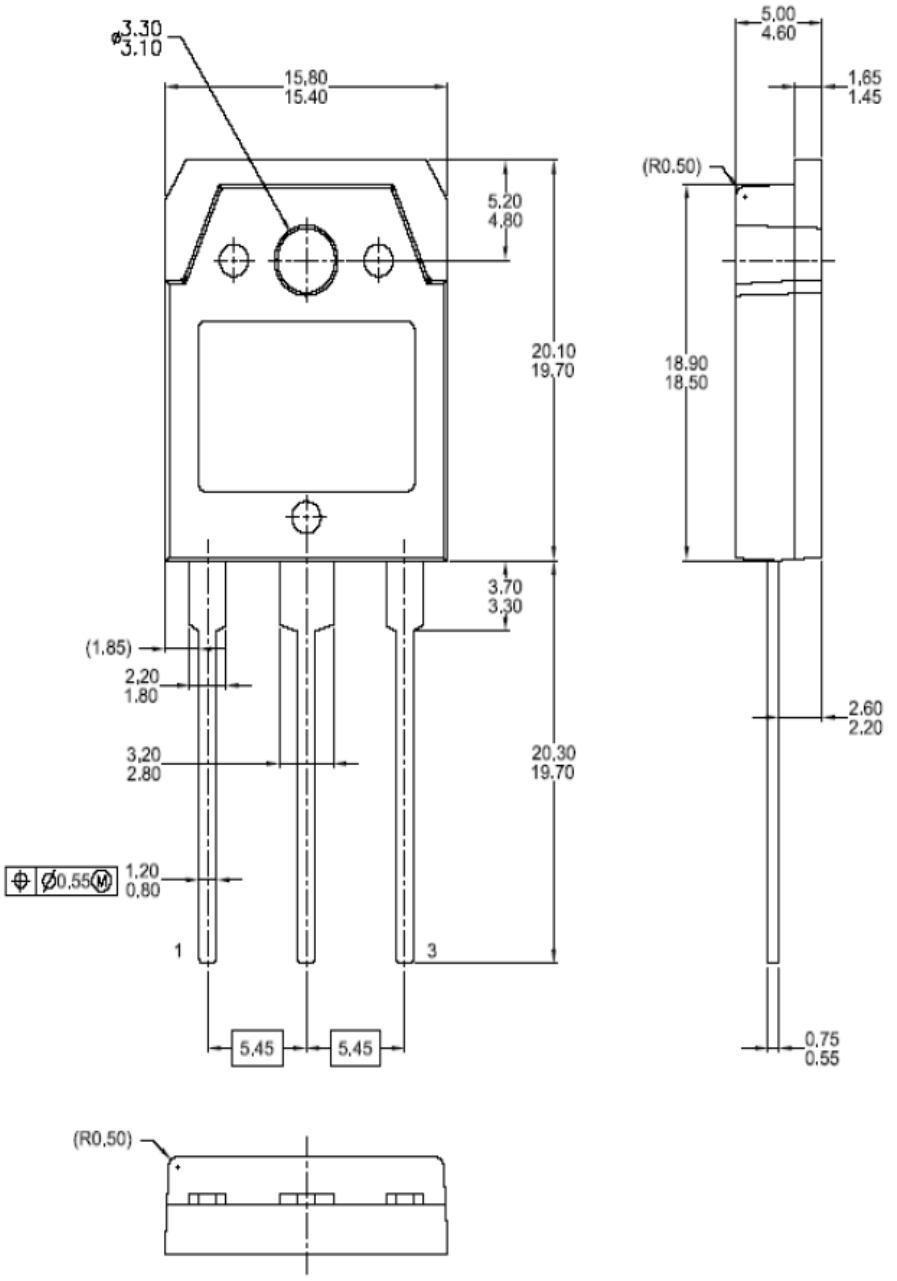
Peak Diode Recovery dv/dt Test Circuit & Waveforms





Mechanical Dimensions

TO-3PN



Dimensions in Millimeters

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